

N-Channel Logic Level Enhancement Mode Field Effect Transistor

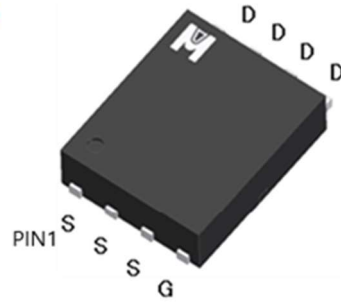
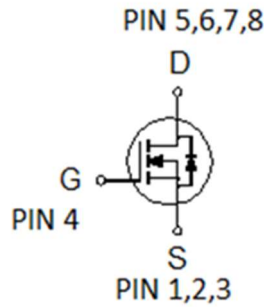
Product Summary:

BV_{DSS}	30V
$R_{DS(on)}$ (MAX.)	1.2m Ω
I_D	200A

N Channel MOSFET

UIS, Rg 100% Tested

Pb-Free Lead Plating & Halogen Free



ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNIT
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ¹	$T_C = 25\text{ }^\circ\text{C}$	I_D	200	A
	$T_A = 25\text{ }^\circ\text{C}$ ($t \leq 10\text{s}$)		55	
	$T_A = 25\text{ }^\circ\text{C}$ (Steady-State)		35	
	$T_C = 100\text{ }^\circ\text{C}$		127	
Pulsed Drain Current ²		I_{DM}	400	
Avalanche Current		I_{AS}	80	
Avalanche Energy	$L = 0.1\text{mH}$, $I_{AS}=80\text{A}$, $R_G=25\Omega$	E_{AS}	320	mJ
Repetitive Avalanche Energy ³	$L = 0.05\text{mH}$	E_{AR}	160	
Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	P_D	83	W
	$T_C = 100\text{ }^\circ\text{C}$		33	
Operating Junction & Storage Temperature Range		T_J, T_{stg}	-55 to 150	$^\circ\text{C}$

100% UIS testing in condition of $V_D=15\text{V}$, $L=0.1\text{mH}$, $V_G=10\text{V}$, $I_L=50\text{A}$, Rated $V_{DS}=30\text{V}$ N-CH

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE		SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Case		$R_{\theta JC}$		1.5	$^\circ\text{C}/\text{W}$
Junction-to-Ambient ³	$t \leq 10\text{s}$	$R_{\theta JA}$		20	
Junction-to-Ambient ³	Steady-State	$R_{\theta JA}$		50	

¹Package Limited.

²Pulse width limited by maximum junction temperature.



³Duty cycle $\leq 1\%$

⁴50°C / W when mounted on a 1 in² pad of 2 oz copper.

ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	30			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1	2	3	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 24V, V _{GS} = 0V			1	μA
		V _{DS} = 20V, V _{GS} = 0V, T _J = 125 °C			25	
On-State Drain Current ¹	I _{D(ON)}	V _{DS} = 10V, V _{GS} = 10V	200			A
Drain-Source On-State Resistance ¹	R _{DS(ON)}	V _{GS} = 10V, I _D = 25A		1	1.2	mΩ
		V _{GS} = 4.5V, I _D = 20A		1.25	1.6	
Forward Transconductance ¹	g _{fs}	V _{DS} = 5V, I _D = 25A		75		S
DYNAMIC						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 15V, f = 1MHz		11245		pF
Output Capacitance	C _{oss}			1212		
Reverse Transfer Capacitance	C _{rss}			1088		
Gate Resistance	R _g	V _{GS} = 15mV, V _{DS} = 0V, f = 1MHz		1.6		Ω
Total Gate Charge ^{1,2}	Q _g (V _{GS} =10V)	V _{DS} = 15V, V _{GS} = 10V, I _D = 25A		174		nC
	Q _g (V _{GS} =4.5V)			85		
Gate-Source Charge ^{1,2}	Q _{gs}			17		
Gate-Drain Charge ^{1,2}	Q _{gd}			30		
Turn-On Delay Time ^{1,2}	t _{d(on)}		V _{DS} = 15V, I _D = 1A, V _{GS} = 10V, R _{GS} = 2.7Ω		20	
Rise Time ^{1,2}	t _r			15		
Turn-Off Delay Time ^{1,2}	t _{d(off)}			65		
Fall Time ^{1,2}	t _f			40		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_C = 25 °C)						
Continuous Current ⁴	I _s				100	A
Pulsed Current ³	I _{SM}				400	
Forward Voltage ¹	V _{SD}	I _F = 25A, V _{GS} = 0V			1.2	V
Reverse Recovery Time	t _{rr}	I _F = I _s , dI _F /dt = 100A / μS		30		nS
Peak Reverse Recovery Current	I _{RM(REC)}			200		A
Reverse Recovery Charge	Q _{rr}			100		nC

¹Pulse test : Pulse Width $\leq 300 \mu\text{sec}$, Duty Cycle $\leq 2\%$.

²Independent of operating temperature.

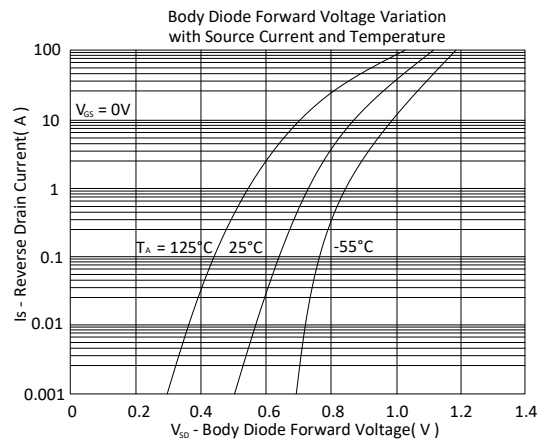
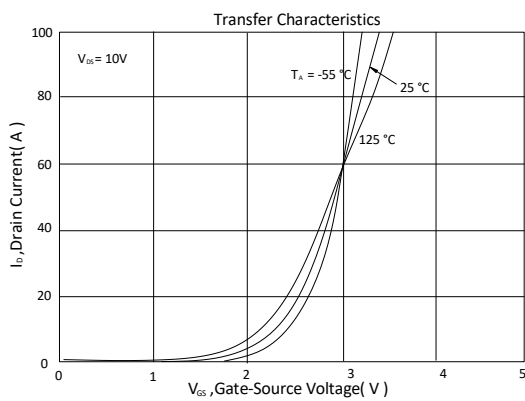
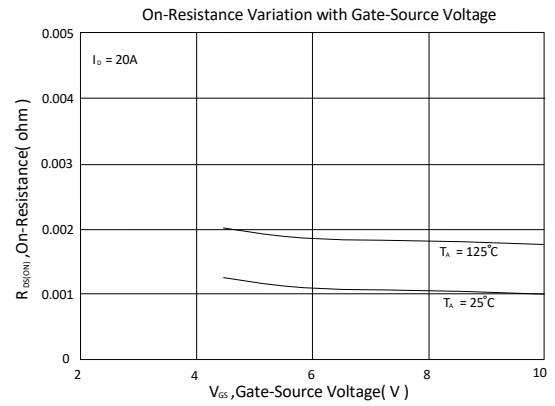
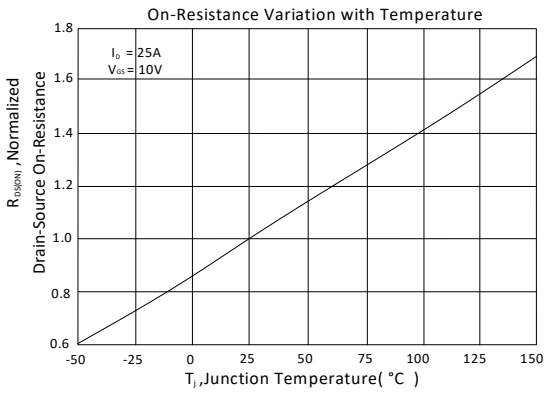
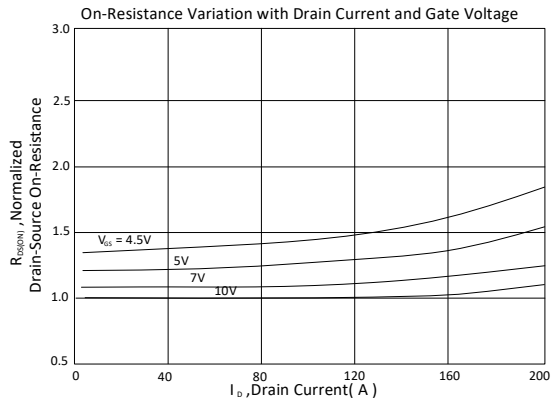
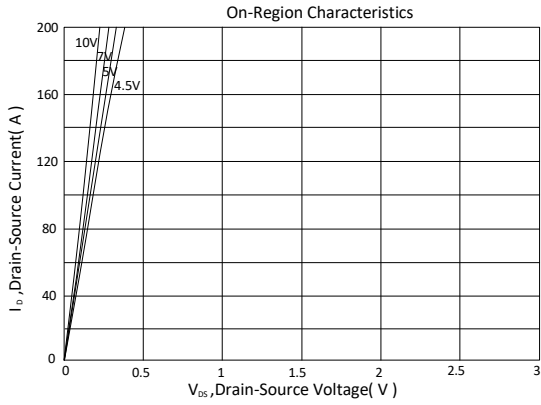
³Pulse width limited by maximum junction temperature.

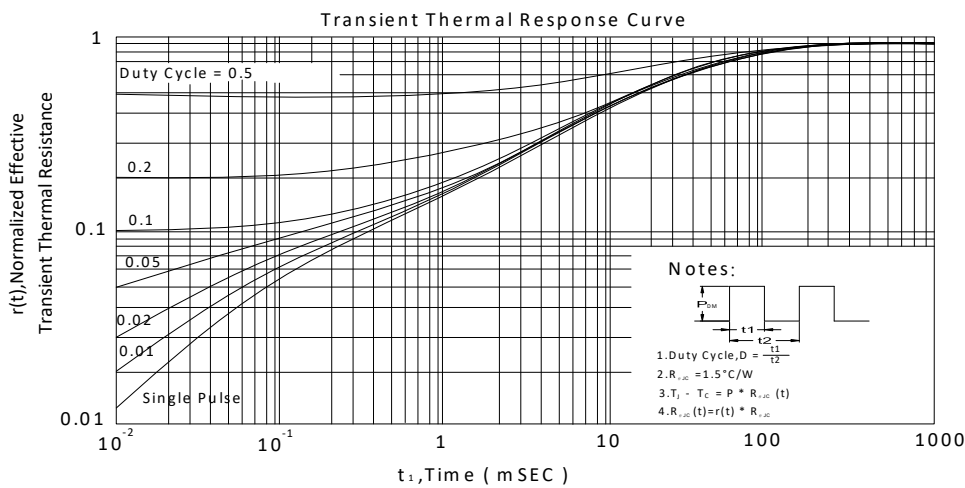
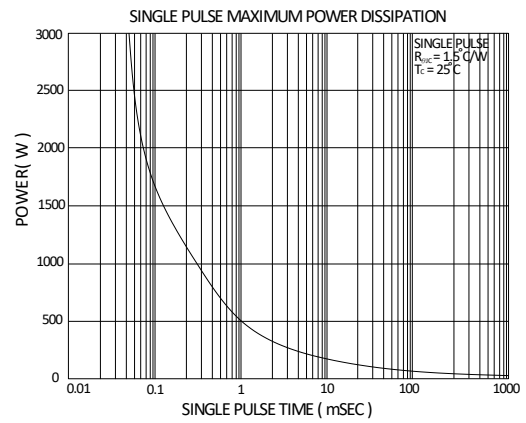
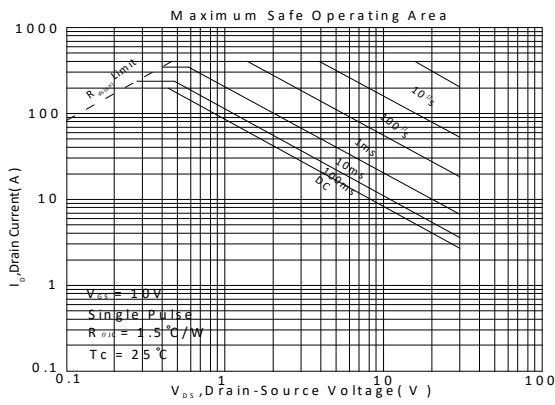
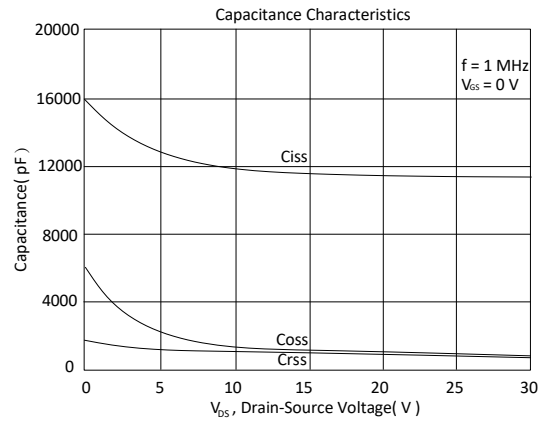
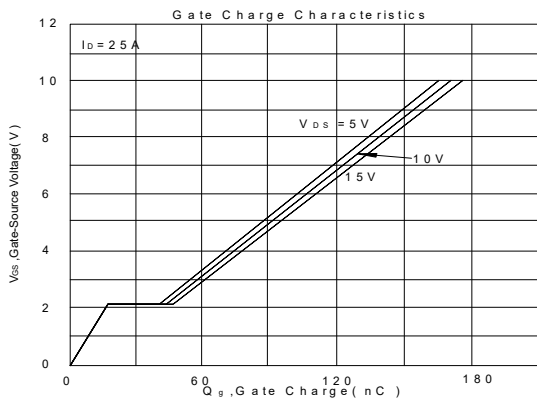
⁴Package Limited.

EMC will review datasheet by quarter, and update new version.



TYPICAL CHARACTERISTICS





Ordering & Marking Information:

Device Name: EMB01N03HR for EDFN5X6



→ EMB01N03HR: Device Name

→ ABCDEFGH: Date Code

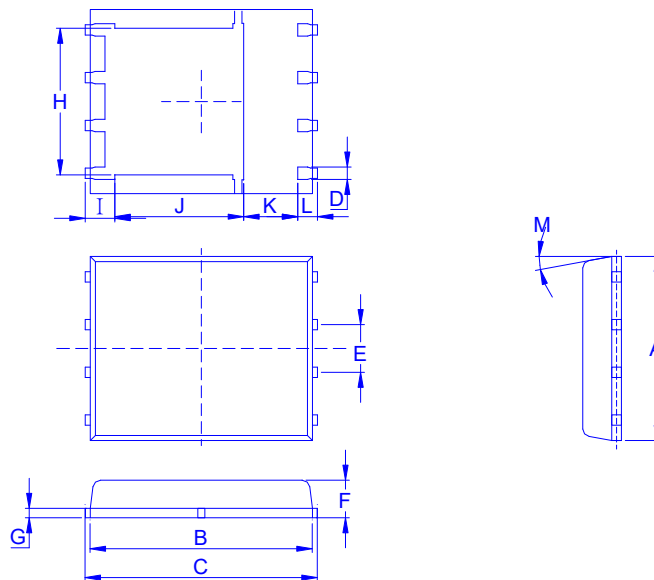
A: Assembly House

B: Year(A:2008 B:2009 C:2010....)

C: Month(A:01 B:02 C:03 D:04 E:05 F:06 G:07 H:08 I:09 J:10 K:11 L:12)

DEFG: Serial No.

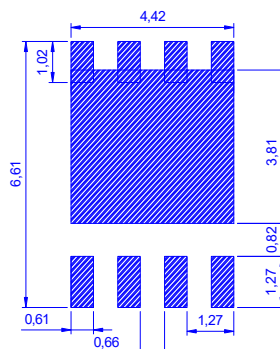
Outline Drawing



Dimension in mm

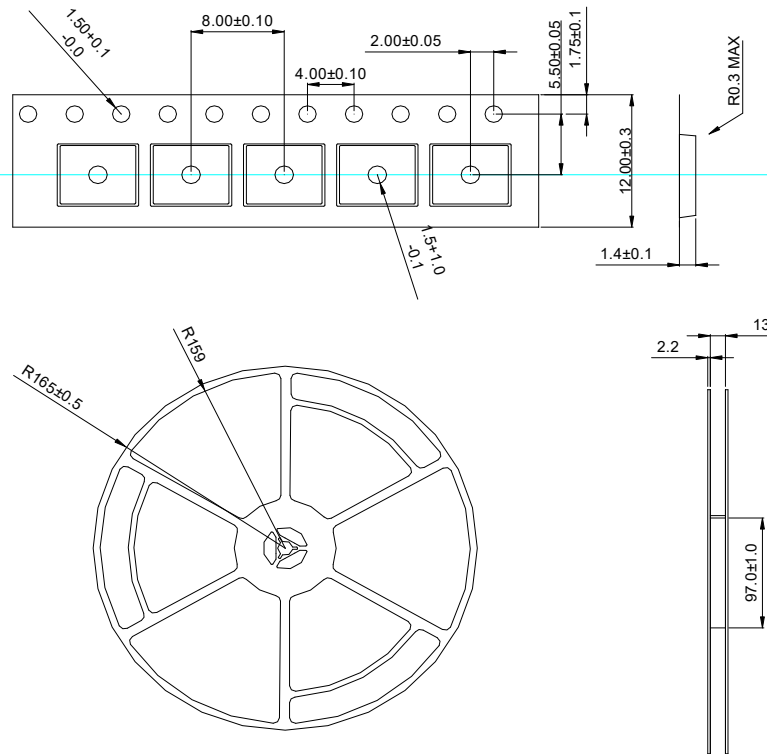
Dimension	A	B	C	D	E	F	G	H	I	J	K	L	M
Min	4.80	5.55	5.90	0.30	1.17	0.85	0.15	3.61	0.38	3.18	1.00	0.38	0°
Typ.	4.90	5.70	6.00	0.40	1.27	0.95	0.20	3.87	0.40	3.44	1.20	0.40	
Max	5.40	5.85	6.15	0.51	1.37	1.17	0.34	4.31	0.71	3.78	1.39	0.71	12°

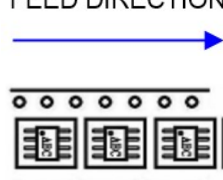
Recommended minimum pads





Tape&Reel Information:2500pcs/Reel(Dimension in millimeter)



產品別	EDFN5X6
Reel 尺寸	13"
編帶方式	FEED DIRECTION 
前空格	25
後空格	50
裝箱數	
滿捲數量	2.5K
捲/內盒比	1 : 1
內盒滿箱數	2.5K
內/外箱比	10 : 1
外箱滿箱數	25K